

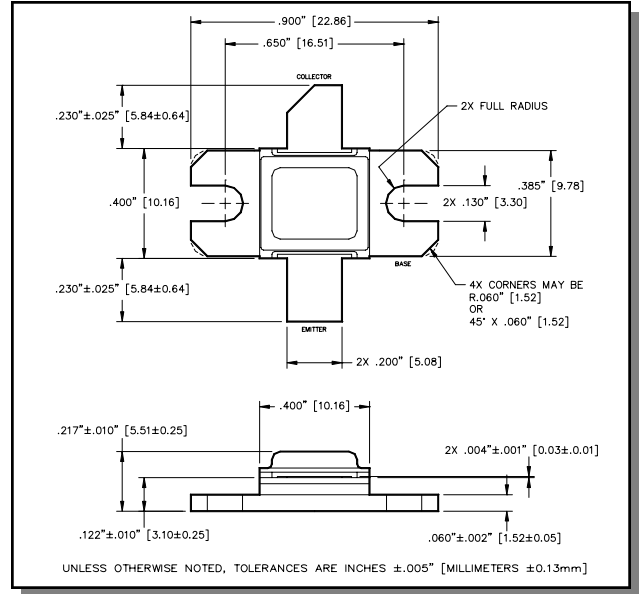
**Radar Pulsed Power Transistor**  
**100W, 1.2-1.4 GHz, 2ms Pulse, 20% Duty**

**M/A-COM Products**  
**Released, 30 May 07**

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	75	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	14.1	A
Power Dissipation @ +25°C	$P_{TOT}$	250	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 50\text{mA}$		$BV_{CES}$	70	-	V
Collector-Emitter Leakage Current	$V_{CE} = 28\text{V}$		$I_{CES}$	-	10	mA
Thermal Resistance	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	0.7	°C/W
Output Power	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$P_{OUT}$	100	-	W
Power Gain	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$G_P$	6.0	-	dB
Collector Efficiency	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$\eta_C$	52	-	%
Input Return Loss	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-8	dB
Load Mismatch Tolerance	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 28\text{V}$ , $P_{in} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

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**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

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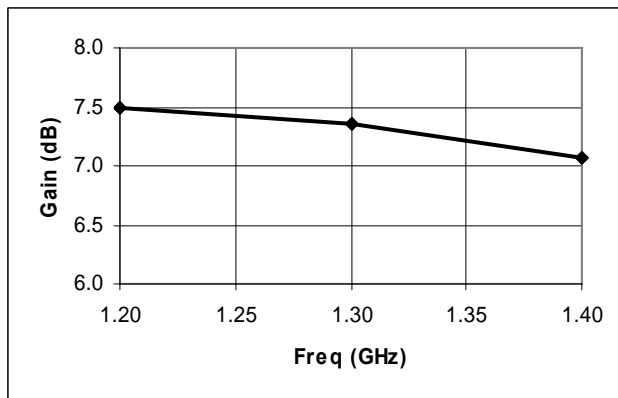
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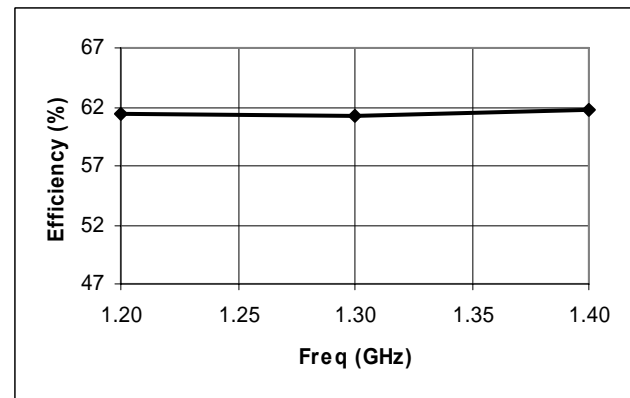
## Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	25	140	7.48	16.3	61.4	-14.9	S	P
1.3	25	136	7.35	15.8	61.3	-13.5	S	P
1.4	25	127	7.07	14.7	61.8	-13.9	S	P

## Gain vs. Frequency

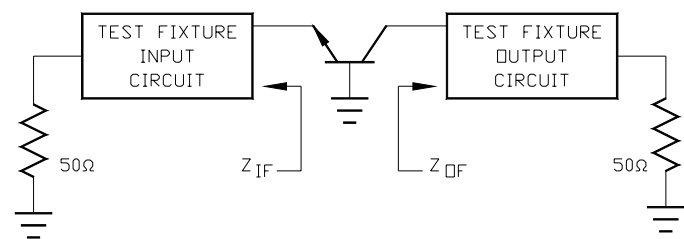


## Collector Efficiency vs. Frequency



## RF Test Fixture Impedance

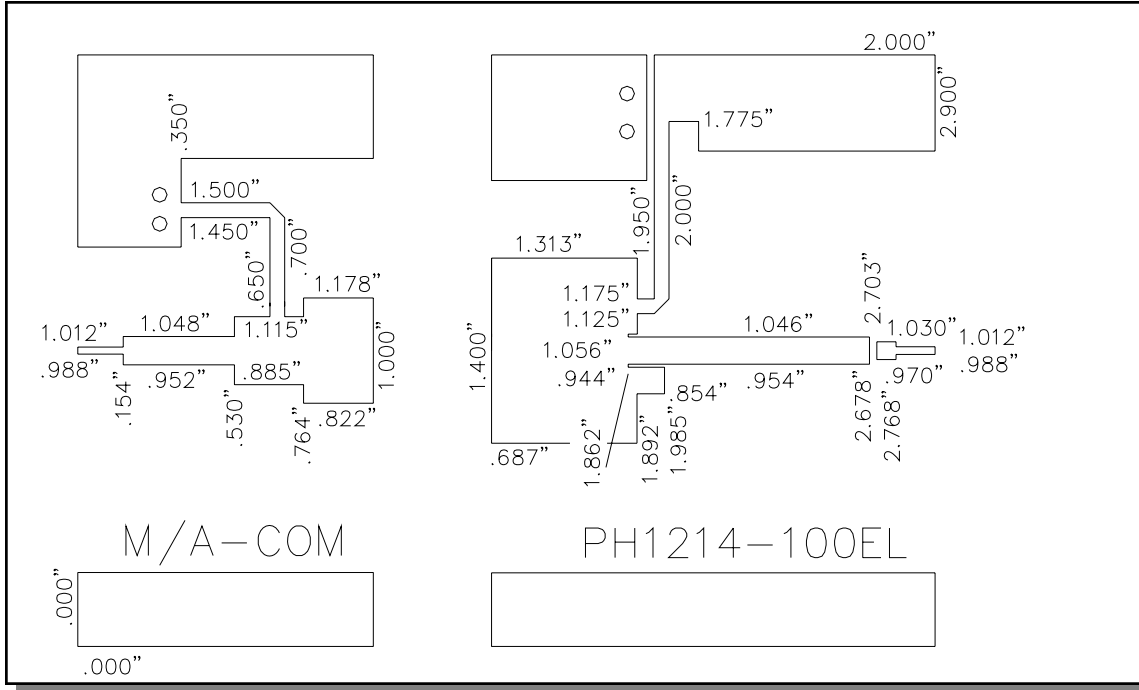
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
1.2	2.6 - j3.8	3.0 - j2.7
1.3	3.0 - j3.4	2.4 - j2.6
1.4	3.4 - j3.1	1.9 - j2.5



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## Test Fixture Circuit Dimensions



## Test Fixture Assembly

